

2020년 2월 13일(목), 09:00~10:30

Room K (다이아몬드 I, 6층)

**D. Thin Film Process Technology 분과**  
**[TK1-D] Thin Film Process I**

<b>TK1-D-1</b> <b>09:00~09:30</b>	<b>[초청]</b> <b>Overview of Atomic Level Patterning Processes</b> Woo-Hee Kim <i>Department of Material Science and Chemical Engineering, Hanyang University</i>
<b>TK1-D-2</b> <b>09:30~09:45</b>	<b>Atomic Layer Modulation for Multicomponent Thin Films</b> Chi Thang Nguyen <sup>1</sup> , Bonwook Gu <sup>1</sup> , Jeyung Ha <sup>1</sup> , Bonggeun Shong <sup>2</sup> , and Han-Bo-Ram Lee <sup>1</sup> <sup>1</sup> <i>Department of Materials Science and Engineering, Incheon National University,</i> <sup>2</sup> <i>Department of Chemical Engineering, Hongik University</i>
<b>TK1-D-3</b> <b>09:45~10:00</b>	<b>Mechanistic Investigation on Atomic Layer Deposition of Group 13 Oxides</b> Abu Saad Ansari, Shimeles Shumi Raya, and Bonggeun Shong <i>Chemical Engineering, Hongik University</i>
<b>TK1-D-4</b> <b>10:00~10:15</b>	<b>Effect of H<sub>2</sub>O and O<sub>3</sub> Reactant Cross Exposure in HfO<sub>2</sub> by Atomic Layer Deposition</b> 고병국, 구본욱, 송세현, Sumaira Yasmeen, Mohammad Rizwan Khan, 이한보람 <i>인천대학교 신소재공학과</i>
<b>TK1-D-5</b> <b>10:15~10:30</b>	<b>Effect of Hydrogen Introduction on Plasma Sulfurization of MoO<sub>3</sub> at Low Temperature</b> Jeong-Hun Choi <sup>1</sup> , Seung-Won Lee <sup>2</sup> , Hyo-Bae Kim <sup>2</sup> , and Ji-Hoon Ahn <sup>1</sup> <sup>1</sup> <i>Department of Materials Science and Chemical Engineering, Hanyang University,</i> <sup>2</sup> <i>Department of Electronic Material Engineering, Korea Maritime &amp; Ocean University</i>